

IN THE SPECIFICATION:

On page 1, after the title and prior to the first full paragraph, which begins at line 2 please insert the following headings and paragraph:

**--Cross Reference To Related Applications**

This application is a continuation of International Application PCT/EP03/07179 having an international filing date of 4 July 2003 and from which priority is claimed under all applicable sections of Title 35 of the United States Code including, but not limited to, Sections 120, 363 and 365(c).

**Technical Field--**

On page 1, prior to line 2, please add the following heading:

**--Background Art--**

On page 1, prior to line 8, please add the following heading:

**--Disclosure of the Invention--**

On page 3, please amend the paragraph beginning on line 3 as follows:

--That object is attained by a semiconductor capacitor as set forth in claim 1 according to the invention, an MOSFET as set forth in claim 7 according to the invention, and a process for the production of a praseodymium silicide layer on a praseodymium oxide layer as set forth in claim 8 according to

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~~the invention. — The appendant claims recite further advantageous configurations of the semiconductor capacitor. --~~

On page 4, please amend the paragraph beginning at line 21 as follows:

--In accordance with a further aspect of the invention there is provided a process for the production of a praseodymium silicide layer on a praseodymium oxide-bearing layer. According to the invention the praseodymium silicide layer is formed by means of local energy input into regions near the surface of the praseodymium oxide-bearing layer by thermal conversion of praseodymium oxide. Preferably the praseodymium oxide-bearing layer is of praseodymium oxide, at least in its regions which are near the surface. The process according to the fourth aspect of the invention has the advantage that a specific deposition step for the production of the praseodymium silicide layer is eliminated. The process is preferably used in conjunction with the production of a semiconductor capacitor ~~as set forth in claim 1 according to the invention, or an MOSFET as set forth in claim 7 according to the invention.~~--

On page 5, prior to line 12, please add the following heading:

--Brief Description of the Drawings--

On page 5, prior to line 7, please add the following heading:

--Detailed Description of The Invention--

On page 8, line 1, please eliminate the heading ("CLAIMS") and replace it with the following:

--What is claimed is:--

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